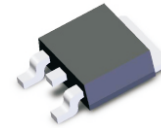


# CDBD2SC6650-G

**Reverse Voltage: 650 V**
**Forward Current: 6 A**
**RoHS Device**


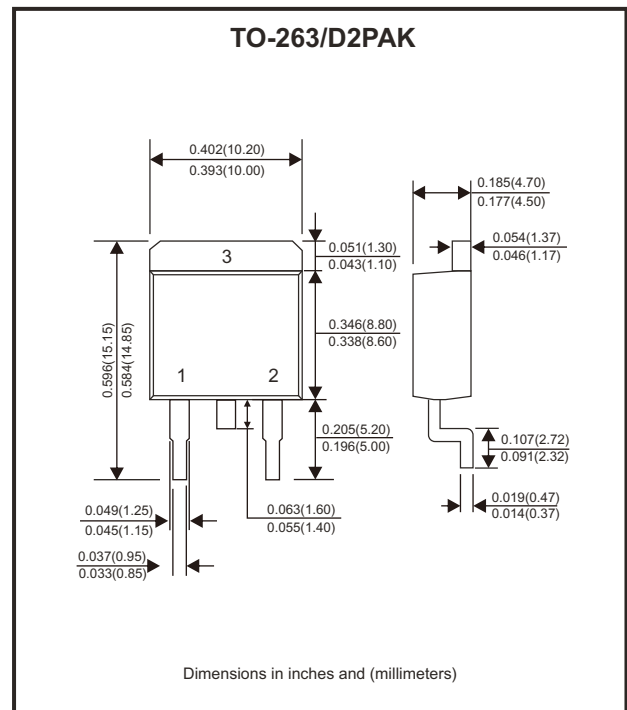
## Features

- Rated to 650V at 6 Amps
- Short recovery time.
- High speed switching possible.
- High frequency operation.
- High temperature operation.
- Temperature independent switching behaviour.
- Positive temperature coefficient on  $V_F$ .

## Mechanical data

- Case: TO-263/D2PAK, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.

## Circuit Diagram



## Maximum Ratings (at $T_A=25^\circ\text{C}$ , unless otherwise noted)

| Parameter                                 | Conditions                                                                  | Symbol          | Value           | Unit               |
|-------------------------------------------|-----------------------------------------------------------------------------|-----------------|-----------------|--------------------|
| Repetitive peak reverse voltage           |                                                                             | $V_{RRM}$       | 650             | V                  |
| Surge peak reverse voltage                |                                                                             | $V_{RSM}$       | 650             | V                  |
| DC blocking voltage                       |                                                                             | $V_{DC}$        | 650             | V                  |
| Continuous forward current                | $T_C = 150^\circ\text{C}$                                                   | $I_F$           | 6               | A                  |
| Repetitive peak forward surge current     | $T_C = 25^\circ\text{C}$ , $t_p = 10\text{ms}$<br>Half sine wave, $D = 0.3$ | $I_{FRM}$       | 30              | A                  |
| Non-repetitive peak forward surge current | $T_C = 25^\circ\text{C}$ , $t_p = 10\text{ms}$<br>Half sine wave            | $I_{FSM}$       | 60              | A                  |
| Power dissipation                         | $T_C = 25^\circ\text{C}$                                                    | $P_{TOT}$       | 85.8            | W                  |
|                                           | $T_C = 110^\circ\text{C}$                                                   |                 | 37.2            |                    |
| Typical thermal resistance                | Junction to case                                                            | $R_{\theta JC}$ | 1.748           | $^\circ\text{C/W}$ |
| Operating junction temperature range      |                                                                             | $T_J$           | $-55 \sim +175$ | $^\circ\text{C}$   |
| Storage temperature range                 |                                                                             | $T_{STG}$       | $-55 \sim +175$ | $^\circ\text{C}$   |

## Electrical Characteristics (at $T_A=25^\circ\text{C}$ , unless otherwise noted)

| Parameter               | Conditions                                                                      | Symbol | Min. | Typ. | Max. | Unit          |
|-------------------------|---------------------------------------------------------------------------------|--------|------|------|------|---------------|
| Forward voltage         | $I_F = 6\text{A}$ , $T_J = 25^\circ\text{C}$                                    | $V_F$  |      | 1.44 | 1.7  | V             |
|                         | $I_F = 6\text{A}$ , $T_J = 175^\circ\text{C}$                                   |        |      | 1.73 | 2.5  |               |
| Reverse current         | $V_R = 650\text{V}$ , $T_J = 25^\circ\text{C}$                                  | $I_R$  |      | 10   | 100  | $\mu\text{A}$ |
|                         | $V_R = 650\text{V}$ , $T_J = 175^\circ\text{C}$                                 |        |      | 15   | 200  |               |
| Total capacitive charge | $V_R = 400\text{V}$ , $T_J = 150^\circ\text{C}$<br>$Q_C = \int_0^{V_R} C(V) dv$ | $Q_C$  |      | 23   |      | nC            |
| Total capacitance       | $V_R = 0\text{V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{MHz}$                | C      |      | 424  | 434  | pF            |
|                         | $V_R = 200\text{V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{MHz}$              |        |      | 44   | 45   |               |
|                         | $V_R = 400\text{V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{MHz}$              |        |      | 42.5 | 43   |               |

## Rating and Characteristics Curves (CDBD2SC6650-G)

Fig.1 - Forward Characteristics

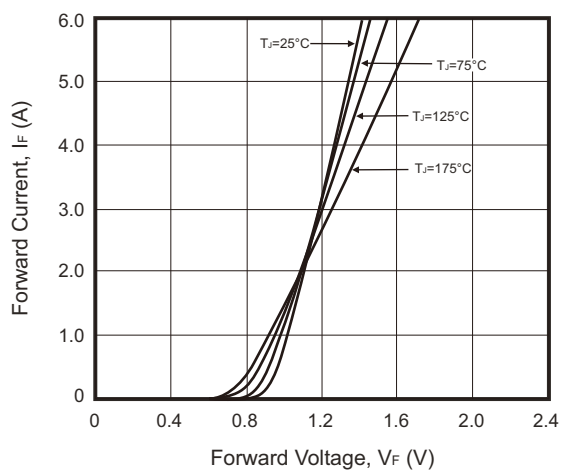


Fig.2 - Reverse Characteristics

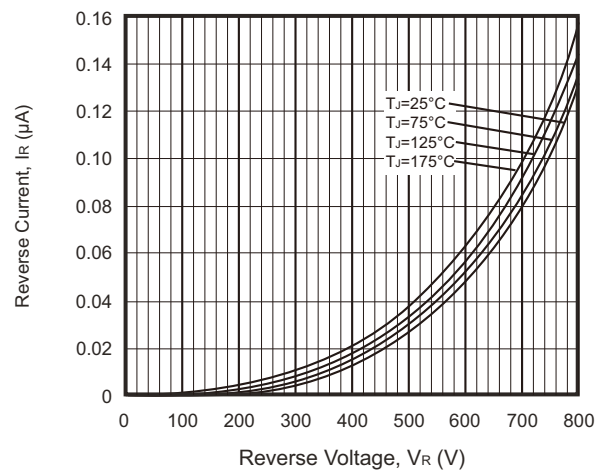


Fig.3 - Current Derating

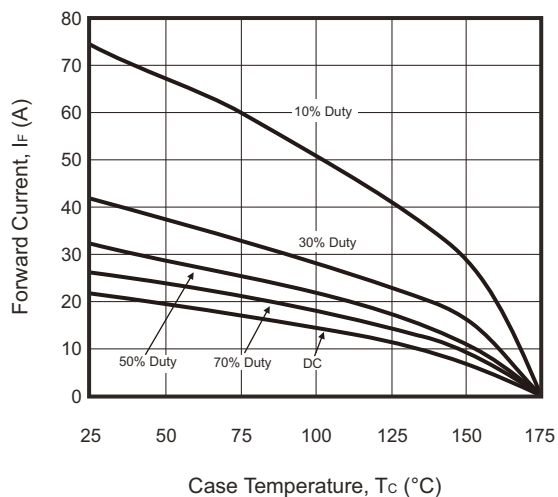
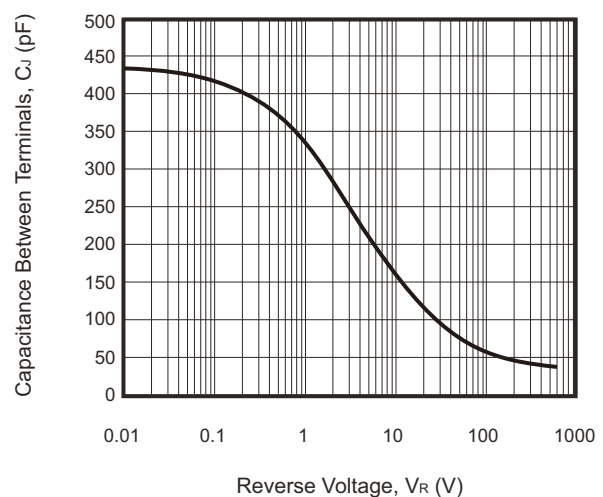
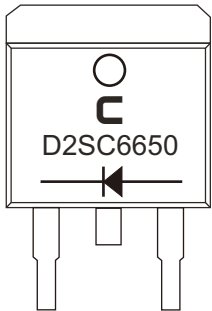


Fig.4 - Capacitance Characteristics



Marking Code

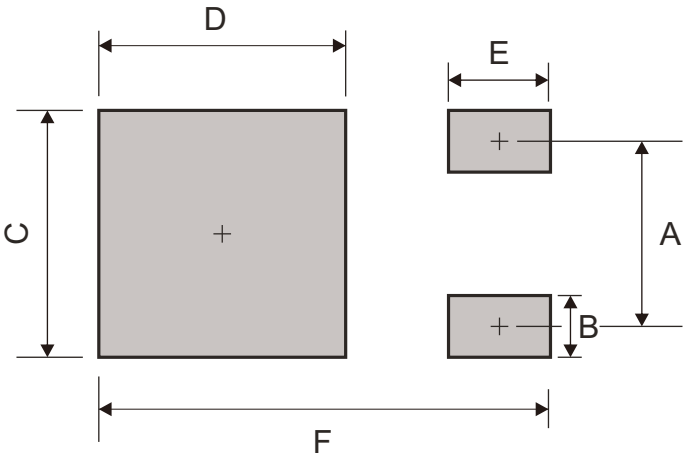
| Part Number   | Marking Code |
|---------------|--------------|
| CDBD2SC6650-G | D2SC6650     |



C = Comchip Logo

Suggested PAD Layout

| SIZE | TO-263 / D2PAK |        |
|------|----------------|--------|
|      | (mm)           | (inch) |
| A    | 5.08           | 0.200  |
| B    | 1.10           | 0.043  |
| C    | 10.80          | 0.425  |
| D    | 8.30           | 0.327  |
| E    | 3.50           | 0.138  |
| F    | 16.90          | 0.665  |



Standard Packaging

| Case Type    | TUBE PACK       |                |
|--------------|-----------------|----------------|
|              | TUBE<br>( pcs ) | BOX<br>( pcs ) |
| TO-263/D2PAK | 50              | 1,000          |